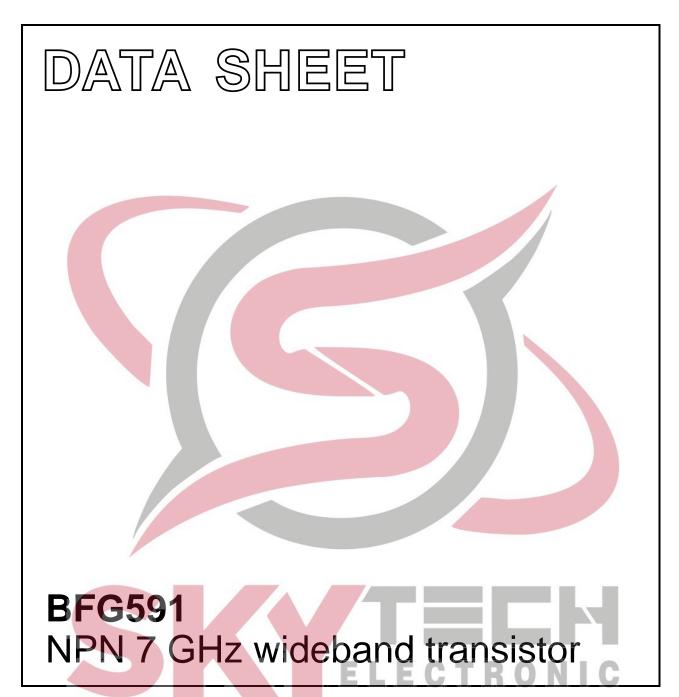
DISCRETE SEMICONDUCTORS



Product specification
Supersedes data of November 1992



NPN 7 GHz wideband transistor

BFG591

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

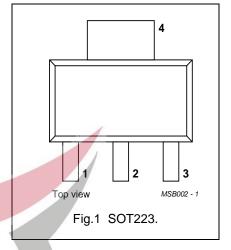
Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscriber equipment.

DESCRIPTION

NPN silicon planar epitaxial transistor in a plastic, 4-pin SOT223 package.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | emitter |
| 2 | base |
| 3 | emitter |
| 4 | collector |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------------------|-------------------------------|---|------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | _ | - | 20 | V |
| V_{CEO} | collector-emitter voltage | open base | _ | - | 15 | V |
| I _C | collector current (DC) | | - | + | 200 | mA |
| P _{tot} | total power dissipation | up to T _s = 80 °C; note 1 | + / | _ | 2 | W |
| h _{FE} | DC current gain | $I_C = 70 \text{ mA}; V_{CE} = 8 \text{ V}$ | 60 | 90 | 250 | |
| C_{re} | feedback capacitance | $I_C = I_c = 0$; $V_{CE} = 12 \text{ V}$; $f = 1 \text{ MHz}$ | 4 | 0.7 | - / | pF |
| f _T | transition frequency | I _C = 70 mA; V _{CE} = 12 V; f = 1 GHz | - / | 7 | | GHz |
| G _{UM} | maximum unilateral power gain | $I_C = 70 \text{ mA}; V_{CE} = 12 \text{ V};$ f = 900 MHz; $T_{amb} = 25 \text{ °C}$ | | 13 | - | dB |
| $\left \mathbf{s}_{21}\right ^2$ | insertion power gain | $I_C = 70 \text{ mA}; V_{CE} = 12 \text{ V};$ f = 900 MHz; $T_{amb} = 25 \text{ °C}$ | _ | 12 | _ | dB |

Note

1. T_s is the temperature at the soldering point of the collector pin.



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--------------------------------------|------|------|------|
| V_{CBO} | collector-base voltage open emitter | | _ | 20 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 15 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 3 | V |
| I _C | collector current (DC) | | - / | 200 | mA |
| P _{tot} | total power dissipation | up to T _s = 80 °C; note 1 | -// | 2 | W |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | -/ | 150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | 34 | CONDITIONS | VALUE | UNIT |
|---------------------|-------------------------------------|----|------------|-------|------|
| R _{th j-s} | thermal resistance from junction to | | note 1 | 35 | K/W |
| | soldering point | | | | |

Note to the Limiting values and Thermal characteristics

1. T_s is the temperature at the soldering point of the collector pin.



NPN 7 GHz wideband transistor

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CHARACTERISTICS

 $T_i = 25$ °C (unless otherwise specified).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------------------|---------------------------------------|---|------|------|------|------|
| V _{(BR)CBO} | collector-base breakdown voltage | $I_C = 0.1 \text{ mA}; I_E = 0$ | 20 | _ | _ | V |
| V _{(BR)CES} | collector-emitter breakdown voltage | $I_C = 10 \text{ mA}; I_B = 0$ | 15 | _ | _ | V |
| V _{(BR)EBO} | emitter-base breakdown voltage | $I_E = 0.1 \text{ mA}; I_C = 0$ | 3 | _ | _ | V |
| I _{CBO} | collector-base leakage current | I _E = 0; V _{CB} = 10 V | _ | - / | 100 | nA |
| h _{FE} | DC current gain | I _C = 70 mA; V _{CE} = 8 V | 60 | 90 | 250 | |
| C _{re} | feedback capacitance | $I_B = I_b = 0$; $V_{CE} = 12 \text{ V}$; $f = 1 \text{ MHz}$ | | 0.7 | _ | pF |
| f⊤ | transition frequency | $I_C = 70 \text{ mA}; V_{CE} = 12 \text{ V};$ f = 1 GHz | | 7 | _ | GHz |
| G _{UM} | maximum unilateral power gain; note 1 | I _C = 70 mA; V _{CE} = 12 V; f = 900 MHz; T _{amb} = 25 °C | - | 13 | _ | dB |
| | | $I_C = 70 \text{ mA}; V_{CE} = 12 \text{ V};$ $f = 2 \text{ GHz}; T_{amb} = 25 ^{\circ}\text{C}$ | - | 7.5 | _ | dB |
| s ₂₁ ² | insertion power gain | I _C = 70 mA; V _{CE} = 12 V; f = 1 GHz; T _{amb} = 25 °C | - | 12 | - | dB |
| Vo | output voltage | note 2 | - | 700 | - | mV |

Notes

1. G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. G_{UM}

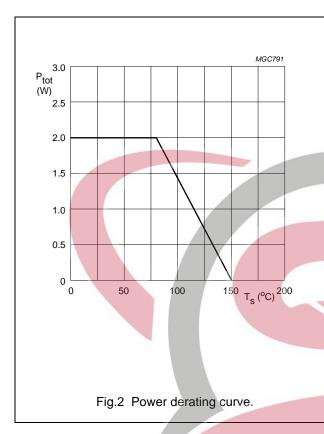
2. $d_{im} = 60 \text{ dB (DIN45004B)};$

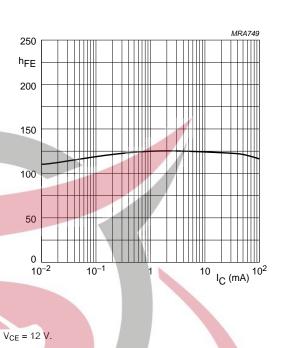
 $\begin{aligned} &V_p = V_{o;} \, V_q = V_o \, -6 \; \text{dB;} \; V_r = V_o \, -6 \; \text{dB;} \\ &f_p = 795.25 \; \text{MHz;} \; f_q = 803.25 \; \text{MHz;} \; f_r = 803.25 \; \text{MHz;} \; \text{measured at} \; f_{(p+q-r)} = 793.25 \; \text{MHz.} \end{aligned}$



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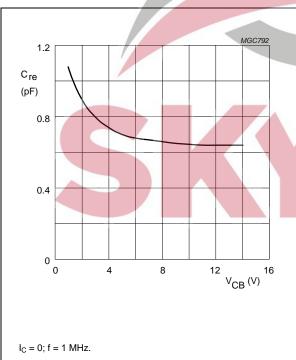
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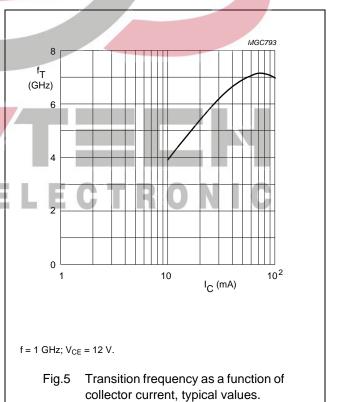




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DC current gain as a function of collector Fig.3 current, typical values.





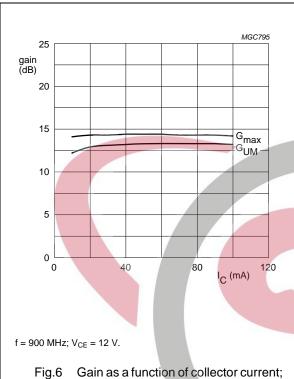
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Fig.4 Feedback capacitance as a function of

collector-base voltage, typical values.

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typical values.

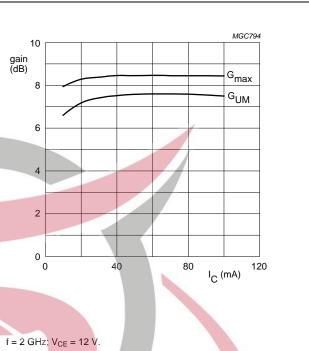


Fig.7 Gain as a function of collector current; typical values.

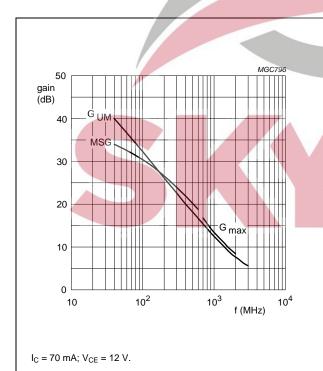


Fig.8 Gain as a function of frequency;

typical values.

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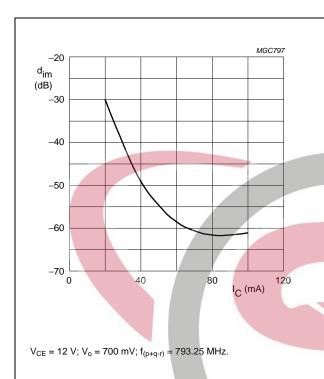
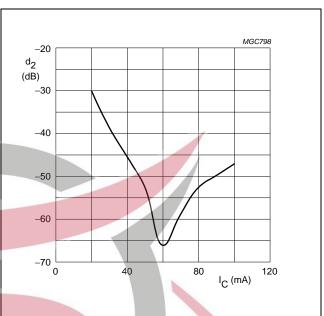


Fig.9 Intermodulation distortion as a function of collector current; typical values.



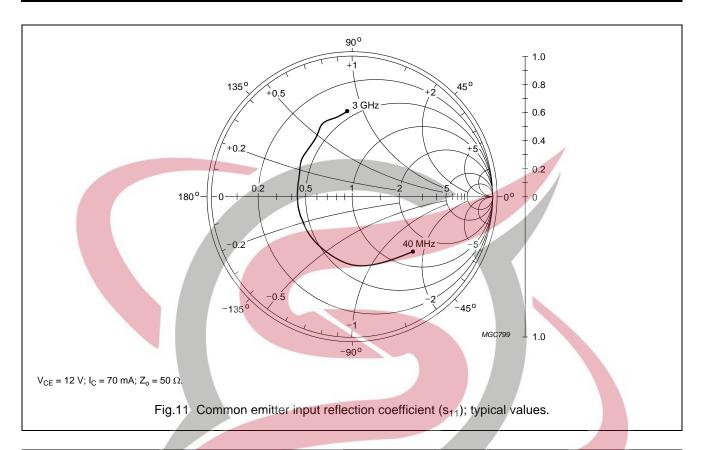
 $V_{CE} = 12 \text{ V; } V_o = 316 \text{ mV; } f_{(p+q)} = 810 \text{ MHz.}$

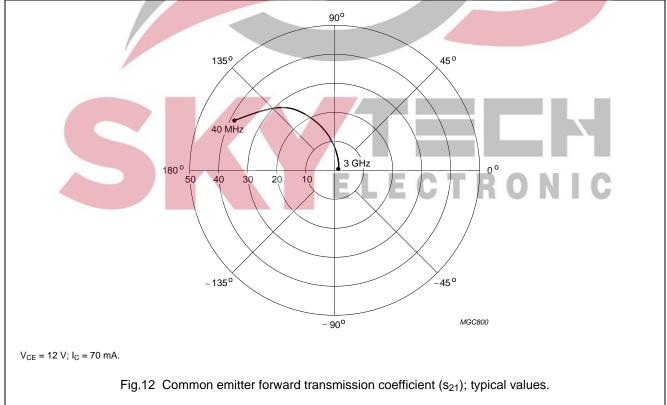
Fig.10 Second order Intermodulation distortion as a function of collector current; typical values.



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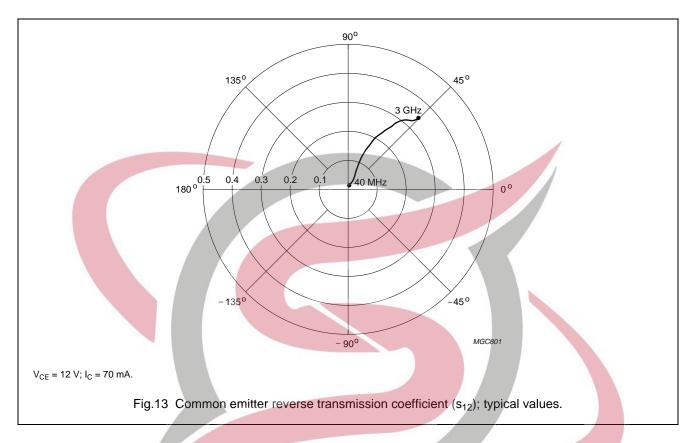
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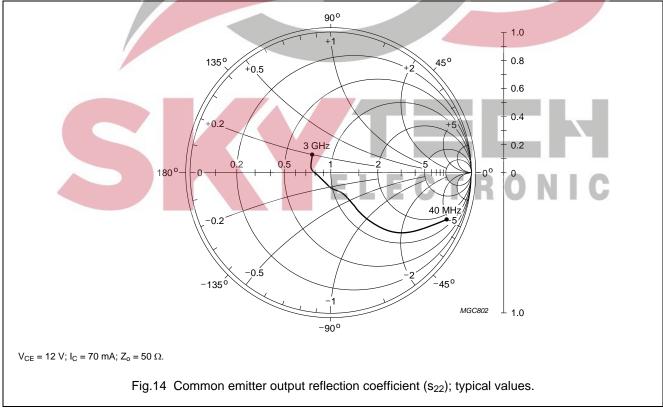




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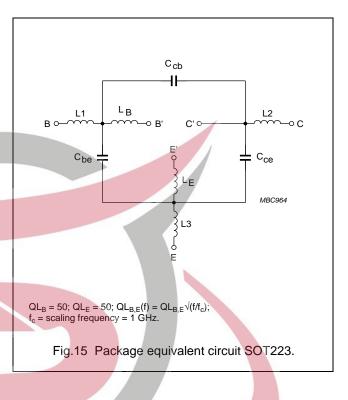


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SPICE parameters for the BFG591 crystal

| SEQUENCE No. | PARAMETER | VALUE | UNIT |
|-------------------|-----------|-------|------|
| 1 | IS | 1.341 | fA |
| 2 | BF | 123.5 | _ |
| 3 | NF | .988 | m |
| 4 | VAF | 75.85 | V |
| 5 | IKF | 9.656 | Α |
| 6 | ISE | 232.2 | fA |
| 7 | NE | 2.134 | - |
| 8 | BR | 10.22 | _ |
| 9 | NR | 1.016 | |
| 10 | VAR | 1.992 | V |
| 11 | IKR | 294.1 | mA |
| 12 | ISC | 211.0 | aA |
| 13 | NC | 997.2 | + ~ |
| 14 | RB | 5.00 | Ω |
| 15 | IRB | 1.000 | μА |
| 16 | RBM | 5.00 | Ω |
| 17 | RE | 1.275 | Ω |
| 18 | RC | 920.6 | mΩ |
| 19 ⁽¹⁾ | XTB | 0.000 | _ |
| 20 (1) | EG | 1.110 | EV |
| 21 (1) | XTI | 3.000 | _ |
| 22 | CJE | 3.821 | pF |
| 23 | VJE | 600.0 | mV |
| 24 | MJE | 348.5 | m |
| 25 | TF | 13.60 | ps |
| 26 | XTF | 71.73 | - / |
| 27 | VTF | 10.28 | V |
| 28 | ITF | 1.929 | А |
| 29 | PTF | 0.000 | deg |
| 30 | CJC | 1.409 | pF |
| 31 | VJC | 219.4 | mV |
| 32 | MJC | 166.5 | m |
| 33 | XCJ | 2.340 | m |
| 34 | TR | 543.7 | ns |
| 35 ⁽¹⁾ | CJS | 0.000 | F |
| 36 (1) | VJS | 750.0 | mV |
| 37 (1) | MJS | 0.000 | _ |
| 38 | FC | 733.2 | m |



List of components (see Fig.15)

| DESIGNATION | VALUE | UNIT |
|-----------------|-------|------|
| C _{be} | 182 | fF |
| C_{cb} | 16 | fF |
| C _{ce} | 249 | fF |
| L1 | 0.025 | nH |
| L2 | 1.19 | nH |
| L3 | 0.60 | nH |
| L _B | 1.50 | nH |
| LECT | 0.50 | nH |

Note

1. These parameters have not been extracted, the default values are shown.

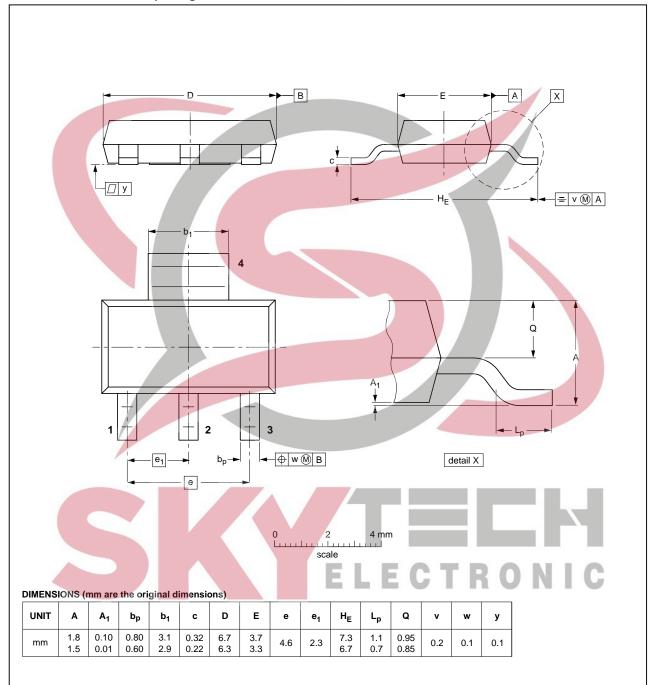
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PACKAGE OUTLINE

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



| OUTLINE | | REFERENCES | | | EUROPEAN ISSUE DATE | |
|---------|-----|------------|-------|--|---------------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT223 | | | SC-73 | | | -04-11-10 06-03-16 |
| | | | | | | |

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| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
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| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
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